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Measurement of energy relaxation in quantum Hall edge states utilizing quantum point contacts

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We demonstrated a method to probe local electronic states and energy relaxation in quantum Hall edge states utilizing quantum point contacts. We evaluated relaxation lengths in the cases with electron tunneling and only with energy exchange between edge states. They were consistent with the results of previous experiments, and we have checked the validity of our method. We applied this method to measure the energy relaxation length around a hotspot in quantum Hall regimes and revealed the possible short-distance relaxation process as the relaxation due to energy exchange between edge states without electron tunneling.

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Edge states in the quantum Hall regime[1] attract strong interests in basic science and application to quantum electronics in semiconductor micro devices. Quantum Hall edge states have long coherence lengths in solids and well defined chiralities.[2,3] By utilizing these properties, interesting electronic devices, e.g. electronic Mach-Zender interferometers,[4,5] single electron sources,[6] etc. have been demonstrated. Also, there are theoretical proposals to use quantum Hall edge states for quantum information applications.[7,8]

In many of the applications, local electronic properties of the edge states play important roles. Recently, experiments probing the local electronic states, non-equilibrium energy distribution and energy relaxation in quantum Hall edge states utilizing quantum dots as local probes have been reported.[9–12] In the experiment, energy relaxation with a short relaxation length (3 μm), which originates from energy exchange between edge channels, was observed and the relaxation mechanism was discussed using a microscopic model.[11] A similar approach has also been used to probe the electronic states in the fractional quantum Hall regime.[13]

In this paper, we measured the local electronic states in quantum Hall edge states using a different kind of probe: quantum point contacts (QPCs).[14,15] We used the QPC probes to investigate the spacial change of the electronic states and evaluated the energy relaxation lengths. By comparing these results with previous experiments, we checked the validity of our method. Next, we applied this method to probe energy relaxation around a specific energy dissipation point, called a "hotspot" in quantum Hall regimes, which is formed near a gate by applying a large bias across the gate to create hot electrons[16]. We revealed the mechanism of the short-distance energy relaxation around the hotspot.

Figure 1(a) shows optical and scanning electron micrographs of the device. The device was fabricated from a GaAs/AlGaAs heterostructure wafer with sheet carrier density 3.9×10^{15} m^{-2} and mobility 52 m^2/Vs at 2 K. The two-dimensional electron gas is formed 60 nm beneath the surface. We patterned a mesa structure by wet-etching and formed Ti/Au Schottky surface gates by deposition. Five QPCs (QPC$_1$ - QPC$_5$) were formed by applying negative voltages on the gates and each QPC was connected to each corresponding Ohmic contact O$_1$ - O$_5$. The distance from QPC$_1$ to QPC$_2$ - QPC$_5$ is 1.0, 3.1, 9.7 and 30.0 μm, respectively.

We applied a magnetic field perpendicular to the wafer surface and created quantum Hall edge states in the mesa. With the magnetic field of 4.05 T, quantum Hall states with filling factor ν=4 were formed in the bulk. At this magnetic field, the spin splitting was not large enough to create fully spin split edge channels in our device at 2 K, so spin-degenerate two edge channels were formed in the device. We injected electrons from the Ohmic contacts O$_0$ and O$_1$ to the edge states, and created a non-equilibrium energy distribution by changing the transmission of QPC$_1$ and the voltages applied on O$_0$, V_0, and O$_1$, V_1, respectively (Fig. 1(b)). We monitored the change of the local electronic states by measuring voltages at the Ohmic contacts O$_2$ to O$_5$. By adjusting the transmission of one of the QPCs, QPC$_n$$(n = 2, 3, \cdots, 5)$, to $2e^2/h$ and the others to 0, the outermost edge channel can interact with only one Ohmic contact O$_n$. The voltage observed at O$_n$, V_n, reflects the local electronic states of the outermost edge channel at the position of QPC$_n$. With changing the distance d from QPC$_1$ by changing n, V_n will be changed, and therefore we

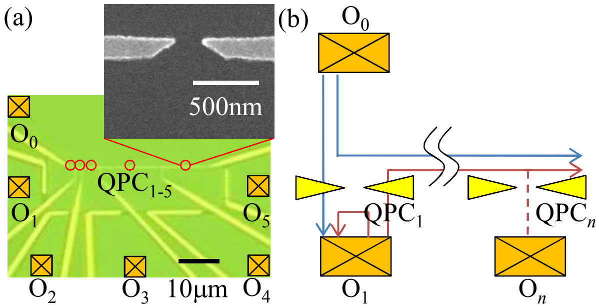

FIG. 1: (color online) (a) Optical and scanning electron micrographs of the device. We prepared five QPCs to initialize and probe the local electronic states in the quantum Hall edge states. (b) Schematic of the device operation. We used QPC$_1$ to create a non-equilibrium electron distribution and QPC$_n$$(n = 2, 3, \cdots, 5)$ to probe the local electronic states of the outermost edge channel.

can get information of the energy relaxation with d.

Energy relaxation in quantum Hall edge states can be classified into two kinds of mechanisms. The first one is tunneling of electrons between edge states.[16,17] If electrons with higher energy tunnel to the edge states with lower electrochemical potential, energy relaxation to make the electrochemical potentials of the edge states equivalent occurs. The other is energy exchange between edge states without tunneling of electrons.[11] There is Coulomb interaction between the edge states and this enables energy exchange between them. Energy relaxation, which equalizes electron temperature of the edge states, occurs in this process.

First, we measured the relaxation length of energy relaxation with electron tunneling. To create a non-equilibrium energy distribution in the edge states which causes energy relaxation with electron tunneling, we connect the inner edge channel to contact O_0 and the outer edge channel to contact O_1 by adjusting the conductance through QPC_1 to $2e^2/h$. We can create a difference in chemical potential μ between the inner and outer edge states by making a difference between V_0 and V_1 (Fig. 2(a)). In this case, electrons in the outer edge channel with higher energy can tunnel into the inner channel contacting O_0. This accompanies energy relaxation. We can measure the relaxation length l_t by monitoring μ of the outer channel through V_n at QPC_2 - QPC_5.

Figure 2(b) shows the measured V_n as a function of d. To normalize the value of V_n as V_1, we plot the numerical derivative of V_n, $\mathrm{d}V_n/\mathrm{d}V_1$. If there is energy relaxation in this range of d, we can observe the decrease of $\mathrm{d}V_n/\mathrm{d}V_1$,[18] however, we observe no such decrease up to $d = 30$ μm. This indicates l_t is much longer than 30 μm. This result is consistent with the previous experiments using local gates with longer distances (over 100 μm).[16,17]

Next, we measured the energy relaxation only with energy exchange between edge channels. To induce such kind of relaxation, we set the conductance through QPC_1 to e^2/h and made half of the electrons in the outer edge channel supplied by O_0 and the remaining half by O_1. This results in the non-equilibrium energy distribution with two Fermi levels in the outer edge channel when we make a difference between V_0 and V_1 (Fig. 3(a)).[9,11] In this case, the energy can be transferred from the outer to the inner edge channel because the outer channel can radiate energy in the process of the relaxation from the non equilibrium energy distribution to the conventional Fermi distribution. We could measure this relaxation length l_e by monitoring V_n of the outer channel at QPC_2 - QPC_5 because the energy relaxation with electron tunneling is negligible on this short scale as we observed in Fig. 2.

Figure 3(b) shows the measured $\mathrm{d}V_n/\mathrm{d}V_1$ as a function of d. We observe that $\mathrm{d}V_n/\mathrm{d}V_1$ abruptly decreases with d. This result shows that we can detect the change of the energy distribution through the change of V_n even in this case.[19] The solid line in Fig. 3(b) is the fitting to the data with a simple exponential decay and the best fitting is obtained for l_e of 3 ± 1 μm. This result is consistent with the previous experiments with quantum dots.[11]

These results support the validity of our measurement method with QPCs. The possible reason why l_e is much smaller than l_t is the following. In the case of relaxation only with energy exchange, the process needs only the interaction to mediate energy transfer between edge channels like the Coulomb interaction and therefore requires a short distance. On the other hand in the case of energy relaxation with electron tunneling, the process needs electron tunneling between spatially separated edge channels, which requires a long distance. Thus, the energy relaxation with energy exchange will first occur and be followed by relaxation with tunneling of electrons on a long scale.

Finally, we applied the method with QPCs to measure the energy relaxation around a hotspot. One kind of hotspot is known to be formed around a QPC when we apply a high bias across the QPC.[16] If the applied bias exceeds the potential barrier formed by the QPC, some electrons pass through the QPC and form hot electrons (Fig. 4(a)). We measured the energy relaxation length around this hotspot with our method and discuss the possible mechanism of the energy relaxation from the information of the relaxation length.

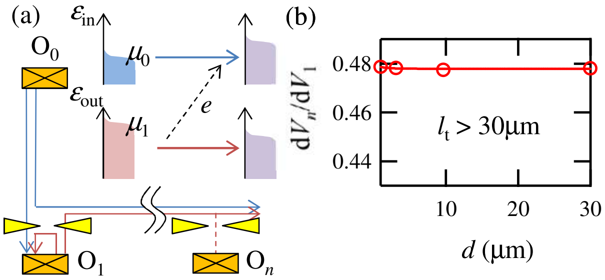

FIG. 2: (color online) (a) Schematic of the experimental setup to probe the energy relaxation with electron tunneling. The conductance of QPC_1 is set to $2e^2/h$. The inner edge channel is connected to O_0 and the outer channel is connected to O_1. We can induce a difference in μ between edge channels by controlling V_0 and V_1. (b) $\mathrm{d}V_n/\mathrm{d}V_1$ as a function of d. No significant relaxation is observed.

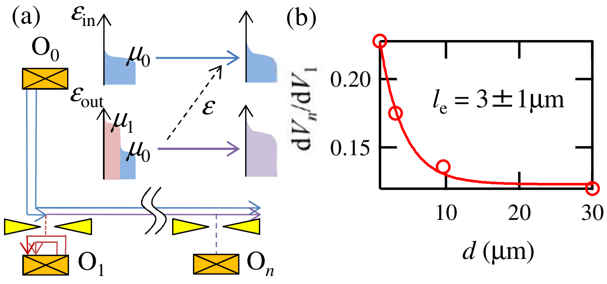

FIG. 3: (color online) (a) Schematic of the experimental setup to probe the energy relaxation with energy exchange. The conductance of QPC_1 is set to e^2/h. The inner edge channel is connected to O_0 and the outer channel is connected to both O_0 and O_1. We can create the non-equilibrium energy distribution with two Fermi energies in the outer edge channel by controlling V_0 and V_1. (b) $\mathrm{d}V_n/\mathrm{d}V_1$ as a function of d. Decay of $\mathrm{d}V_n/\mathrm{d}V_1$ is observed. The solid line is the result of fitting.

Figure 4(b) is the obtained results of $\mathrm{d}V_n/\mathrm{d}V_1$ as a function of d. We applied a high bias (up to 10 mV, which exceeds the potential barrier formed by the QPC of sub meV) on O_1 to create a hotspot next to QPC_1. The $\mathrm{d}V_n/\mathrm{d}V_1$ abruptly decreases with d, indicating that there is energy relaxation on this length scale. The solid line in Fig. 4(b) is the best fit to the data with the relaxation length l_h of $2 \pm 1 \mu$m. This value is comparable with l_e and we can conclude the possible mechanism of the energy relaxation on this length scale around the hotspot is the exchange of energy between edge states.

In conclusion, we have measured the energy relaxation length of the quantum Hall edge channels utilizing QPCs. We confirmed the relaxation length with electron tunneling as $> 30\ \mu$m and the relaxation length with energy exchange as $3 \pm 1\ \mu$m. From these results, we have checked the validity of our detection method. We applied this method to measure energy relaxation around a hotspot and revealed that the possible mechanism is the energy exchange between edge channels.

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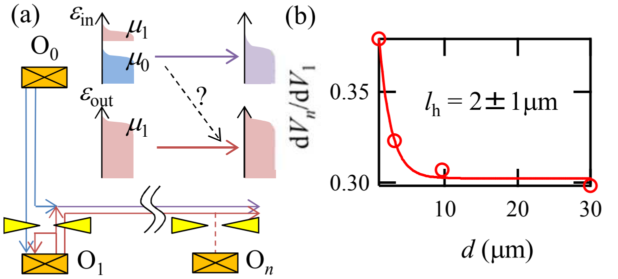

FIG. 4: (color online) (a) Schematic of the experimental setup to probe energy relaxation around a hotspot. We set the conductance of QPC_1 to $2e^2/h$ and applied high bias across QPC_1 to form a hotspot. The inner edge channel has hot electrons supplied by O_1. (b) $\mathrm{d}V_n/\mathrm{d}V_1$ as a function of d. Decay of $\mathrm{d}V_n/\mathrm{d}V_1$ is observed. The solid line is the result of the fitting.

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[18] The absolute value of $\mathrm{d}V_n/\mathrm{d}V_1$ is affected by the contact resistances of Ohmic contacts. The real voltages applied on the edge states become smaller than the value applied on the contact because of the resistance. If the value of the Ohmic resistance is small, $\mathrm{d}V_n/\mathrm{d}V_1$ is close to 1 in the case without energy relaxation. In this device, however, the value is relatively large as a few kΩ and $\mathrm{d}V_n/\mathrm{d}V_1$ becomes smaller than 1 even without energy relaxation.

[19] We think the effect of the specific density of states (DOS) of the quantum Hall edge states is a possible mechanism of the correlation between the electron temperature and V_n. The DOS below the Fermi level will be enhanced because of the electron-electron interaction in the edge states and the nonlinearity of the confinement potential at the device edge.[20,21] With the increase of the electron temperature and the broadening of the energy distribution in the edge states, the required V_n to realize the equilibrium condition with the edge states will be reduced to compensate for the high DOS below the Fermi level in the edge states.

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